

BC849CW,135 Datasheet



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DiGi Electronics Part Number BC849CW,135-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number BC849CW,135

Description TRANS NPN 30V 0.1A SOT323

Detailed Description Bipolar (BJT) Transistor NPN 30 V 100 mA 100MHz 2

00 mW Surface Mount SOT-323



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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
BC849CW,135	Nexperia USA Inc.
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
NPN	100 mA
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
30 V	600mV @ 5mA, 100mA
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
15nA (ICBO)	420 @ 2mA, 5V
Power - Max:	Frequency - Transition:
200 mW	100MHz
Operating Temperature:	Grade:
150°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q101	Surface Mount
Package / Case:	Supplier Device Package:
SC-70, SOT-323	SOT-323
Base Product Number:	
BC849	

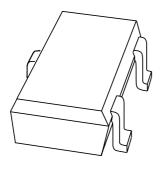
Environmental & Export classification

8541.21.0075

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	

DISCRETE SEMICONDUCTORS

DATA SHEET



BC849W; BC850W NPN general purpose transistors

Product data sheet Supersedes data of 1997 Jun 20 1999 Apr 12



NPN general purpose transistors

BC849W; BC850W

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 45 V).

APPLICATIONS

• Low noise stages in tape recorders, hi-fi amplifiers and other audio-frequency equipment.

DESCRIPTION

NPN transistor in a SOT323 plastic package. PNP complements: BC859W and BC860W.

MARKING

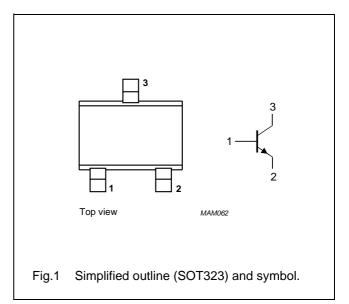
TYPE NUMBER	MARKING CODE ⁽¹⁾	TYPE NUMBER	MARKING CODE ⁽¹⁾		
BC849BW	2B*	BC850BW	2F*		
BC849CW	2C*	BC850CW	2G*		

Note

* = - : Made in Hong Kong.
 * = t : Made in Malaysia.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BC849W		_	30	V
	BC850W		_	50	V
V _{CEO}	collector-emitter voltage	open base			
	BC849W		_	30	V
	BC850W		_	45	V
V _{EBO}	emitter-base voltage	open collector	_	5	V
I _C	collector current (DC)		_	100	mA
I _{CM}	peak collector current		_	200	mA
I _{BM}	peak base current		_	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

NPN general purpose transistors

BC849W; BC850W

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	625	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = 30 V	_	_	15	nA
		I _E = 0; V _{CB} = 30 V; T _j = 150 °C	_	_	5	μΑ
I _{EBO}	emitter cut-off current	I _C = 0; V _{EB} = 5 V	_	_	100	nA
h _{FE}	DC current gain	$I_C = 2 \text{ mA}$; $V_{CE} = 5 \text{ V}$; see Figs 2 and 3				
	BC849BW; BC850BW		200	_	450	
	BC849CW; BC850CW		420	_	800	
V _{CEsat}	collector-emitter saturation	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	_	_	250	mV
	voltage	I _C = 100 mA; I _B = 5 mA; note 1	_	_	600	mV
V _{BE}	base-emitter voltage	I _C = 2 mA; V _{CE} = 5 V	580	_	700	mV
		I _C = 10 mA; V _{CE} = 5 V	_	_	770	mV
C _c	collector capacitance	I _E = i _e = 0; V _{CB} = 10 V; f = 1 MHz	_	_	3	pF
C _e	emitter capacitance	$I_C = i_c = 0$; $V_{EB} = 500 \text{ mV}$; $f = 1 \text{ MHz}$	_	11	_	pF
f _T	transition frequency	I _C = 10 mA; V _{CE} = 5 V; f = 100 MHz	100	_	_	MHz
F	noise figure	I_C = 200 μA; V_{CE} = 5 V; R_S = 2 kΩ; f = 10 Hz to 15.7 kHz	_	_	4	dB
		I_C = 200 μA; V_{CE} = 5 V; R_S = 2 kΩ; f = 1 kHz; B = 200 Hz	_	_	4	dB

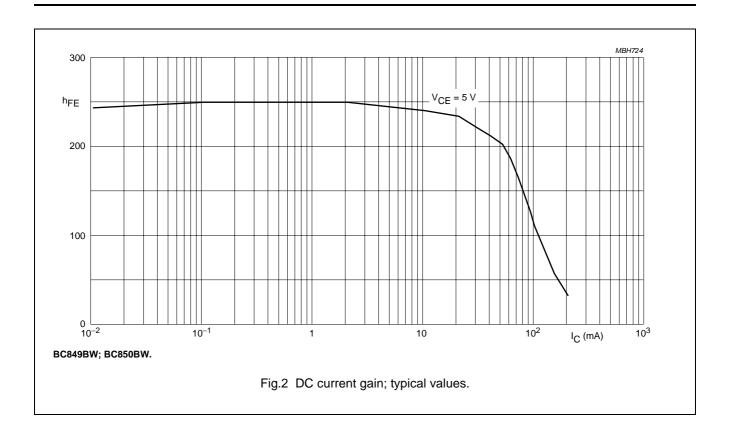
Note

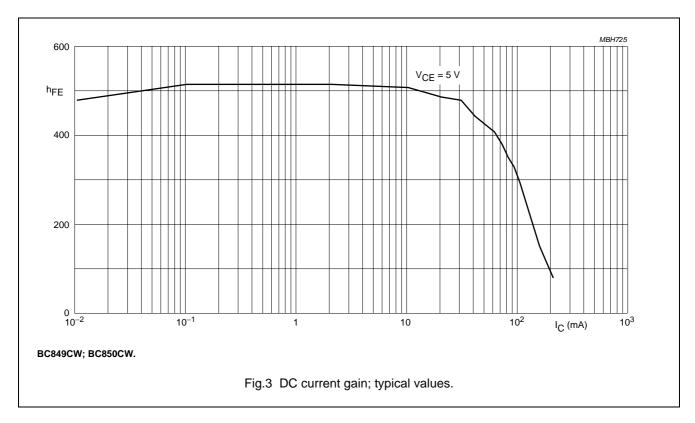
1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

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NPN general purpose transistors

BC849W; BC850W





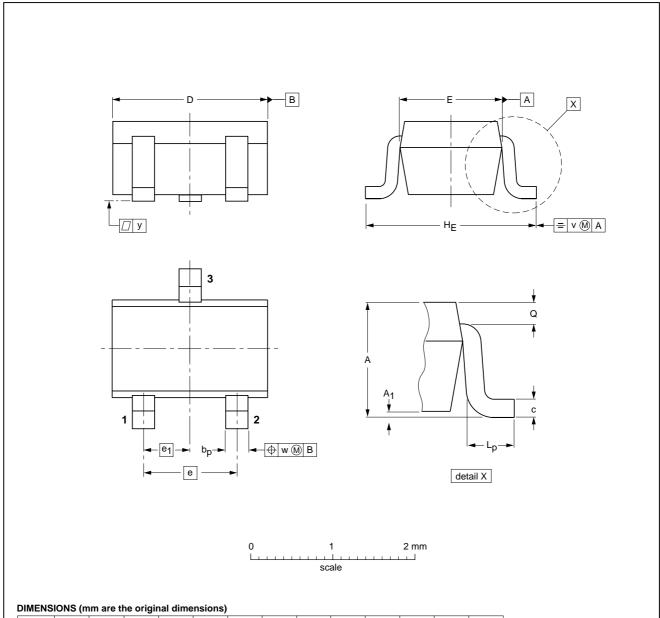
NPN general purpose transistors

BC849W; BC850W

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



UNIT	Α	A ₁ max	bp	С	D	E	е	e ₁	HE	Lp	Q	v	w	
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2	

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE		
VERSION	IEC	IEC JEDEC		IEC JEDEC EIAJ		PROJECTION	ISSUE DATE
SOT323			SC-70			97-02-28	

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1999 Apr 12

NPN general purpose transistors

BC849W; BC850W

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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